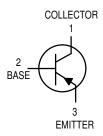
Amplifier Transistors PNP Silicon



MAXIMUM RATINGS

Rating	Symbol	BC 307	BC 308C	BC 309	Unit
Collector-Emitter Voltage	V _{CEO}	-45	-25	-25	Vdc
Collector-Base Voltage	V _{CBO}	-50	-30	-30	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0			Vdc
Collector Current — Continuous	IC	-100		mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8		mW mW/°C	
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = -2.0 mAdc, I _B = 0)	BC307 BC308C BC309B	V _(BR) CEO	–45 –25 –25	 - 	_ _ _	Vdc	
Emitter-Base Breakdown Voltage ($I_E = -100 \mu Adc$, $I_C = 0$)	BC307 BC308C BC309B	V _{(BR)EBO}	-5.0 -5.0 -5.0	_ _ _	_ _ _	Vdc	
Collector–Emitter Leakage Current (VCES = -50 V, VBE = 0) (VCES = -30 V, VBE = 0)	BC307 BC308C BC309B	ICES	_ _ _	-0.2 -0.2 -0.2	-15 -15 -15	nAdc	
$(V_{CES} = -50 \text{ V}, V_{BE} = 0) \text{ TA} = 125^{\circ}\text{C}$	BC307		_	-0.2	-4.0	μΑ	
$(V_{CES} = -30 \text{ V}, V_{BE} = 0) T_{A} = 125^{\circ}\text{C}$	BC308C BC309B		_ _	-0.2 -0.2	-4.0 -4.0		

BC307,B,C BC308C BC309B





BC307,B,C BC308C BC309B

Characteristic		Symbol	Min	Тур	Max	Unit	
ON CHARACTERISTICS							
DC Current Gain ($I_C = -10 \mu Adc$, $V_{CE} = -5.0 Vdc$)	BC307B/309B BC307C/308C	hFE		150 270		_	
$(I_{C} = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307 BC308C		120 120	_	800 800		
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC307B/309B BC307C/308C		200 420	290 500	460 800		
	BC307B/309B BC307C/308C		_	180 300	_ _		
Collector-Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -10$ mAdc, $I_B = see$ Note 1) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc)		VCE(sat)	_ _ _	-0.10 -0.30 -0.25	-0.3 -0.6 	Vdc	
Base-Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc) (I _C = -100 mAdc, I _B = -5.0 mAdc)		V _{BE(sat)}		-0.7 -1.0	_ _	Vdc	
Base–Emitter On Voltage (I _C = -2.0 mAdc, V _{CE} = -5.0 Vdc)		V _{BE(on)}	-0.55	-0.62	-0.7	Vdc	
DYNAMIC CHARACTERISTICS		•		•			
Current-Gain — Bandwidth Product (I _C = -10 mAdc, V _{CE} = -5.0 Vdc, f = 100 MHz)	BC307 BC308C BC309B	fT	_ _ _	280 320 360	_ _ _	MHz	
Common Base Capacitance (V _{CB} = -10 Vdc, I _C = 0, f = 1.0 MHz)		C _{cbo}	_	_	6.0	pF	
Noise Figure $ \begin{array}{l} \text{Noise Figure} \\ \text{(IC = -0.2 mAdc, V_{CE} = -5.0 Vdc,} \\ \text{RS = 2.0 k$\Omega, f = 1.0 kHz)} \\ \text{(IC = -0.2 mAdc, V_{CE} = -5.0 Vdc,} \\ \text{RS = 2.0 k$\Omega, f = 1.0 kHz, f = 200 Hz)} \end{array} $	BC309 BC307 BC308C BC309B	NF	_ _ _ _	2.0 2.0 2.0 2.0	4.0 10 10 4.0	dB	

^{1.} $I_C = -10$ mAdc on the constant base current characteristic, which yields the point $I_C = -11$ mAdc, $V_{CE} = -1.0$ V.

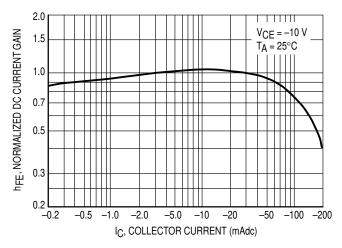


Figure 1. Normalized DC Current Gain

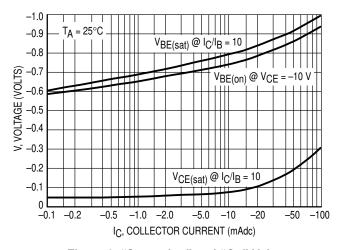


Figure 2. "Saturation" and "On" Voltages



Figure 3. Current-Gain — Bandwidth Product

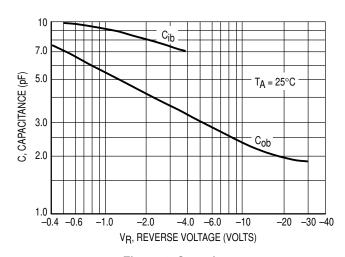


Figure 4. Capacitances

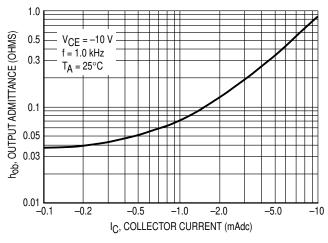


Figure 5. Output Admittance

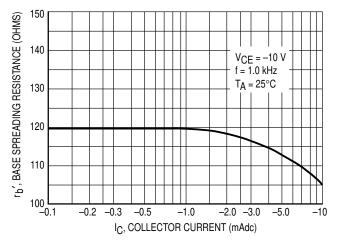
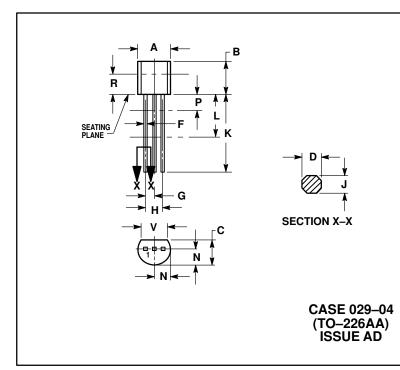


Figure 6. Base Spreading Resistance

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 DIMENSION F APPLIES BETWEEN P AND L.
- DIMENSION P APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
V	0 135		3 43		

STYLE 17: PIN 1. COLLECTOR

- BASE
- 3. EMITTER

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